

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Leonard Forbes		ECH		
SILICON-GERMANIUM DEVICE EPITAXIAL REGROWTH	S FOR CMOS FORMED BY ION IMPLANTATION A	'o	字 P P	HANE H
303.229US2	Serial No.: 09/132,157		5	NE
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Mark V. Prenty	Group Art Unit: 2822	-	ū	
or Patents		208		
	SILICON-GERMANIUM DEVICE EPITAXIAL REGROWTH 303.229US2 August 11, 1998 Mark V. Prenty	SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION A EPITAXIAL REGROWTH 303.229US2 Serial No.: 09/132,157 August 11, 1998 Due Date: April 9, 2003 Mark V. Prenty Group Art Unit: 2822 or Patents	SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SO EPITAXIAL REGROWTH 303.229US2 August 11, 1998 Due Date: April 9, 2003 Mark V. Prenty Group Art Unit: 2822	SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLED P EPITAXIAL REGROWTH 303.229US2 August 11, 1998 Due Date: April 9, 2003 Mark V. Prenty or Patents

Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

 $\frac{X}{X}$ A return postcard.

An Amendment and Response (10 Pages).

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

Atty: David C. Peterson Reg. No. 47,857

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 9 day of April, 2003.

Name

Customer Number 21186

P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900) SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. (GENERAL)

S/N 09/132157

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Leonard Forbes

Examiner: Mark Prenty

Serial No.:

09/132157

Group Art Unit: 2822

Filed:

August 11, 1998

Docket No.: 303.229US2

Title:

SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION

IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on <u>January 9, 2003</u>. Please enter the following remarks.

PATENT RESPONSE

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